THE DATASHEET OF

MAC8SDG

MAC8SDG, MAC8SMG, MAC8SNG

Sensitive Gate Triacs

Silicon Bidirectional Thyristors

Designed for industrial and consumer applications for full wave control of ac loads such as appliance controls, heater controls, motor controls, and other power switching applications.

Features

- Sensitive Gate Allows Triggering by Microcontrollers and other Logic Circuits
- Uniform Gate Trigger Currents in Three Quadrants; Q1, Q2, and Q3
- High Immunity to dv/dt − 25 V/μs Minimum at 110°C
- High Commutating di/dt − 8.0 A/ms Minimum at 110°C
- Maximum Values of I_{GT}, V_{GT} and I_H Specified for Ease of Design
- On−State Current Rating of 8 Amperes RMS at 70°C
- High Surge Current Capability − 70 Amperes
- Blocking Voltage to 800 Volts
- Rugged, Economical TO−220 Package
- These Devices are Pb−Free and are RoHS Compliant*

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off−State Voltage (Note 1) (T_J = −40 to 110°C, Sine Wave, 50 to 60 Hz, Gate Open) MAC8SD MAC8SM MAC8SN	V_{DRM}, V_{RRM}	 400 600 800	V
On-State RMS Current (Full Cycle Sine Wave, 60 Hz, T_C = 70°C)	$I_{T(RMS)}$	8.0	A
Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, T_J = 110°C)	I_{TSM}	70	A
Circuit Fusing Consideration (t = 8.3 ms)	I^2t	20	A^2sec
Peak Gate Power (Pulse Width ≤ 1.0 μs, T_C = 70°C)	P_{GM}	16	W
Average Gate Power (t = 8.3 ms, T_C = 70°C)	$P_{G(AV)}$	0.35	W
Operating Junction Temperature Range	T_J	−40 to +110	°C
Storage Temperature Range	T_{stg}	−40 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor®

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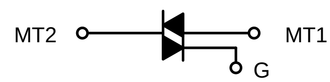
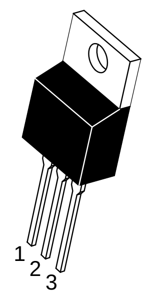
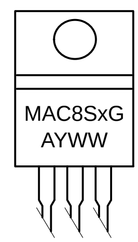
TRIACS
8 AMPERES RMS
400 thru 800 VOLTS





TO−220
CASE 221A
STYLE 4

MARKING DIAGRAM



x	=	D, M, or N
A	=	Assembly Location
Y	=	Year
WW	=	Work Week
G	=	Pb−Free Package

PIN ASSIGNMENT	
1	Main Terminal 1
2	Main Terminal 2
3	Gate
4	Main Terminal 2

ORDERING INFORMATION

Device	Package	Shipping
MAC8SDG	TO−220 (Pb−Free)	50 Units / Rail
MAC8SMG	TO−220 (Pb−Free)	50 Units / Rail
MAC8SNG	TO−220 (Pb−Free)	50 Units / Rail

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction−to−Case Junction−to−Ambient	$R_{\theta JC}$ $R_{\theta JA}$	2.2 62.5	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8″ from Case for 10 Seconds	T_L	260	°C

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted; Electricals apply in both directions)

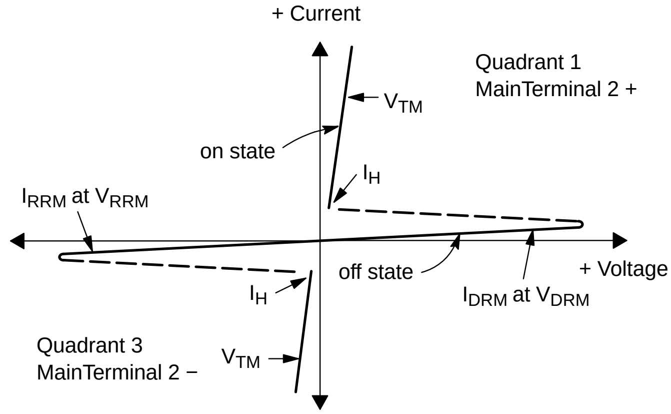
Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Peak Repetitive Blocking Current (V_D = Rated V_{DRM}, V_{RRM}; Gate Open) T_J = 25°C T_J = 110°C	I_{DRM}, I_{RRM}	− −	− −	0.01 2.0	mA
ON CHARACTERISTICS					
Peak On-State Voltage (Note) (I_{TM} = ±11A)	V_{TM}	−	−	1.85	V
Gate Trigger Current (Continuous dc) (V_D = 12 V, R_L = 100 Ω) MT2(+), G(+) MT2(+), G(−) MT2(−), G(−)	I_{GT}	− − −	2.0 3.0 3.0	5.0 5.0 5.0	mA
Holding Current (V_D = 12V, Gate Open, Initiating Current = ±150mA)	I_H	−	3.0	10	mA
Latching Current (V_D = 24V, I_G = 5mA) MT2(+), G(+) MT2(−), G(−) MT2(+), G(−)	I_L	− − −	5.0 10 5.0	15 20 15	mA
Gate Trigger Voltage (Continuous dc) (V_D = 12 V, R_L = 100 Ω) MT2(+), G(+) MT2(+), G(−) MT2(−), G(−)	V_{GT}	0.45 0.45 0.45	0.62 0.60 0.65	1.5 1.5 1.5	V
DYNAMIC CHARACTERISTICS					
Rate of Change of Commutating Current V_D = 400 V, I_{TM} = 3.5 A, Commutating dv/dt = 10 V μ/sec, Gate Open, T_J = 110°C, f = 500 Hz, Snubber: C_S = 0.01 μF, R_S =15 Ω, (See Figure 16)	$di/dt_{(c)}$	8.0	10	−	A/ms
Critical Rate of Rise of Off-State Voltage (V_D = Rate V_{DRM}, Exponential Waveform, R_{GK} = 510 Ω, T_J = 110°C)	dv/dt	25	75	−	V/μs

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

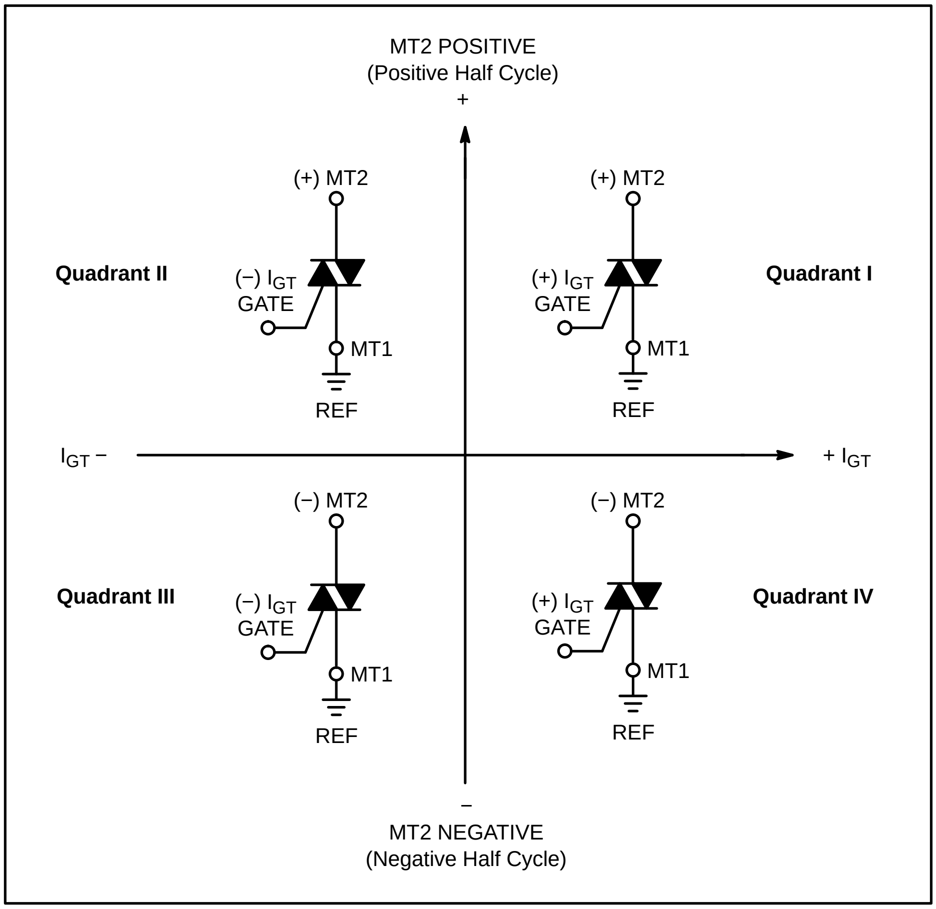
2. Indicates Pulse Test: Pulse Width ≤ 2.0 ms, Duty Cycle ≤ 2%.

Voltage Current Characteristic of Triacs
(Bidirectional Device)

Symbol	Parameter
V_{DRM}	Peak Repetitive Forward Off State Voltage
I_{DRM}	Peak Forward Blocking Current
V_{RRM}	Peak Repetitive Reverse Off State Voltage
I_{RRM}	Peak Reverse Blocking Current
V_{TM}	Maximum On State Voltage
I_H	Holding Current



Quadrant Definitions for a Triac



All polarities are referenced to MT1.
With in−phase signals (using standard AC lines) quadrants I and III are used.

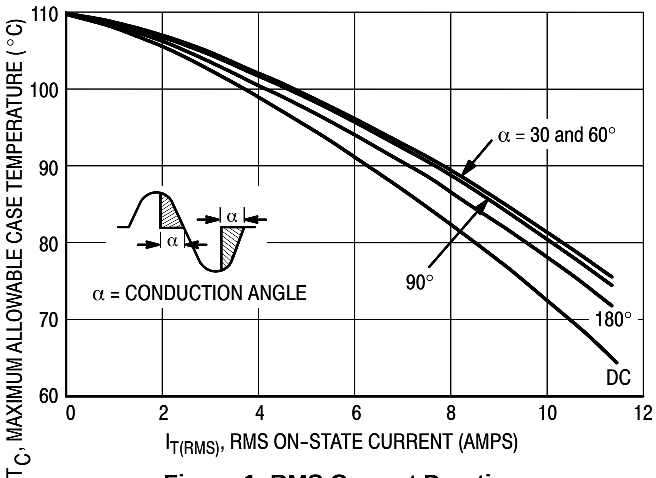


Figure 1. RMS Current Derating

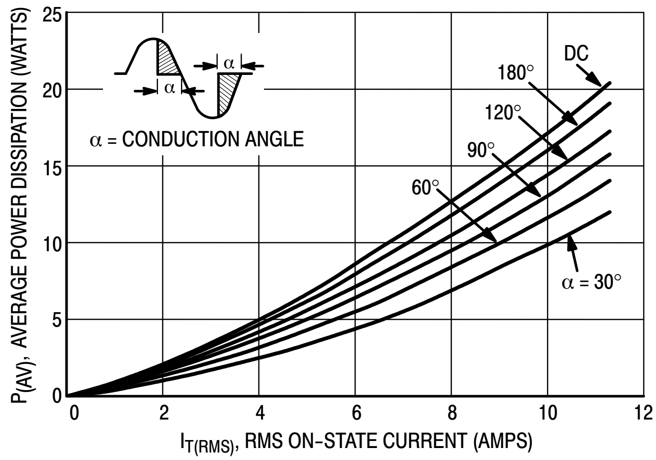


Figure 2. Maximum On−State Power Dissipation

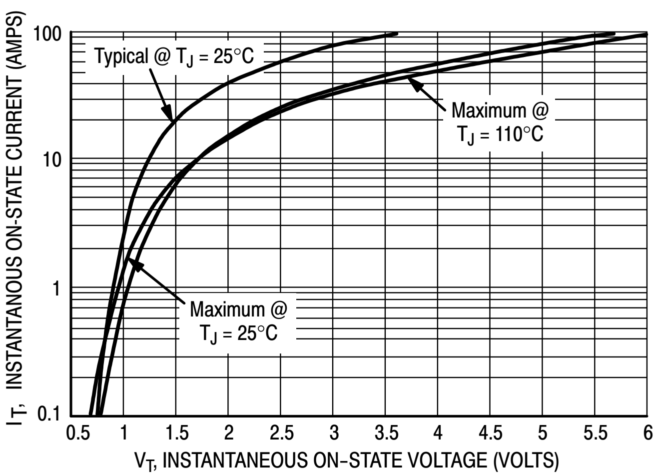


Figure 3. On−State Characteristics

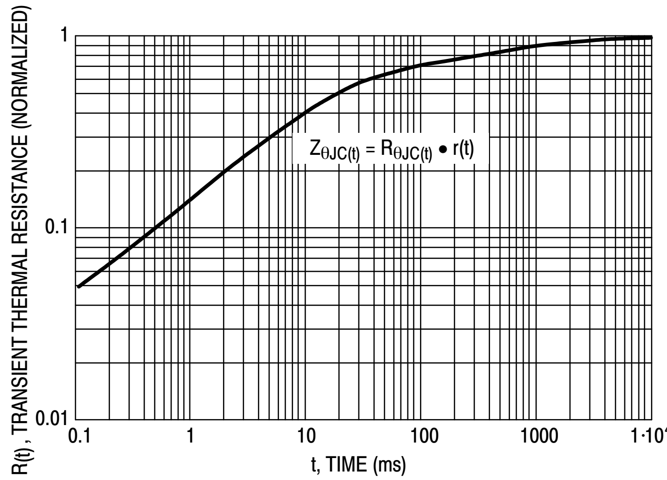


Figure 4. Transient Thermal Response

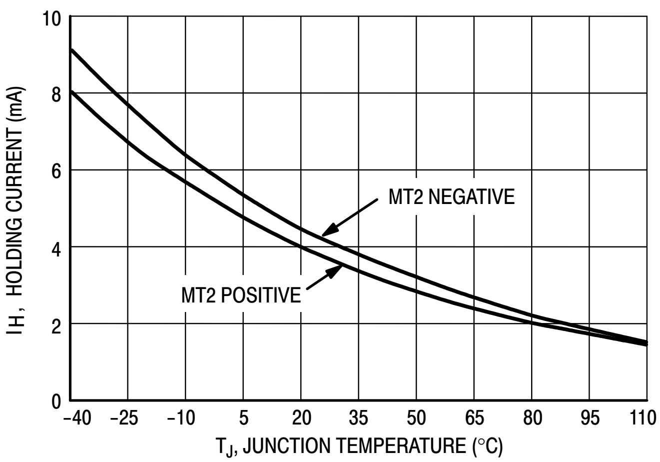


Figure 5. Typical Holding Current Versus Junction Temperature

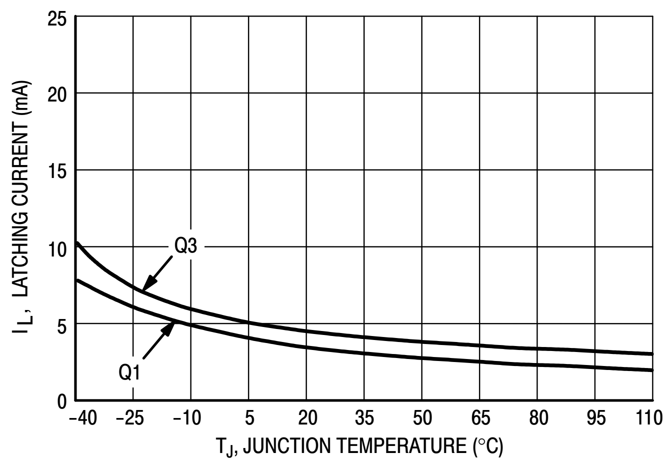


Figure 6. Typical Latching Current Versus Junction Temperature

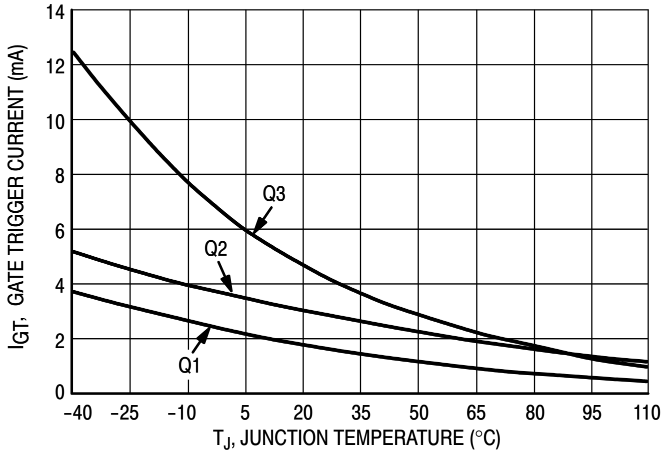


Figure 7. Typical Gate Trigger Current Versus Junction Temperature

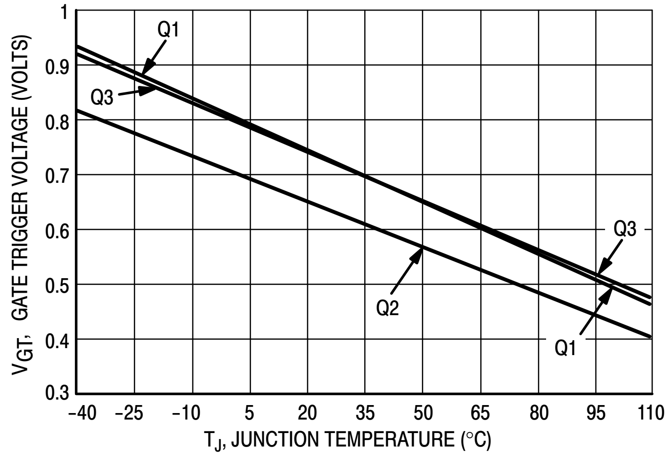


Figure 8. Typical Gate Trigger Voltage Versus Junction Temperature

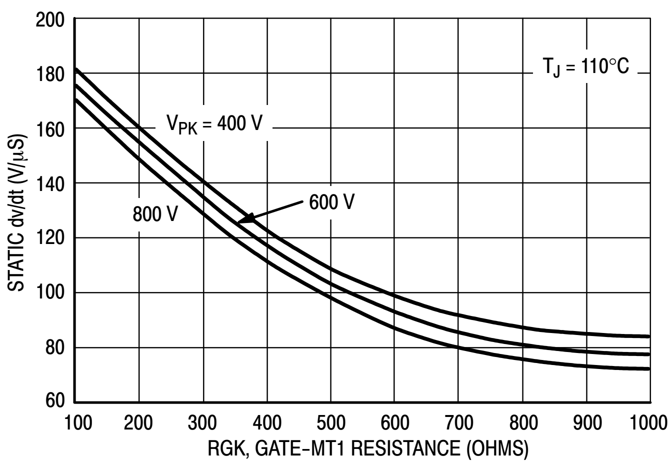


Figure 9. Typical Exponential Static dv/dt Versus Gate−MT1 Resistance, MT2(+)

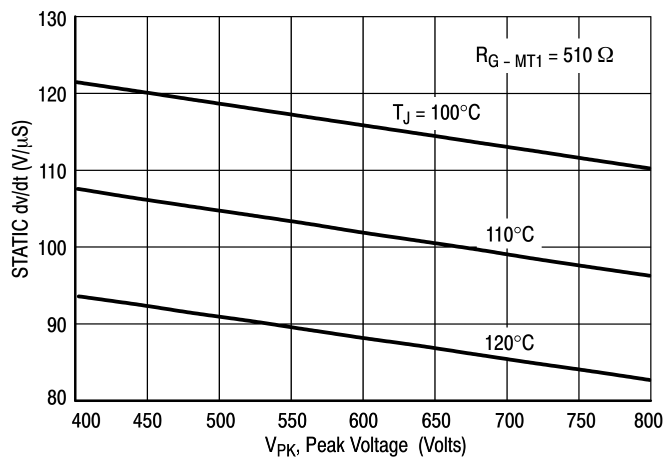


Figure 10. Typical Exponential Static dv/dt Versus Peak Voltage, MT2(+)

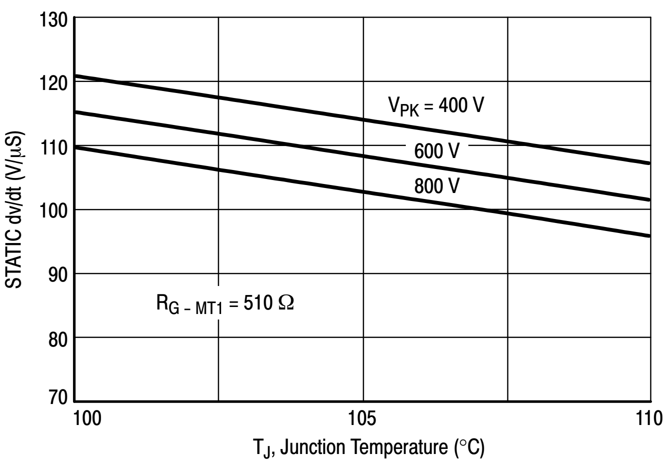


Figure 11. Typical Exponential Static dv/dt Versus Junction Temperature, MT2(+)

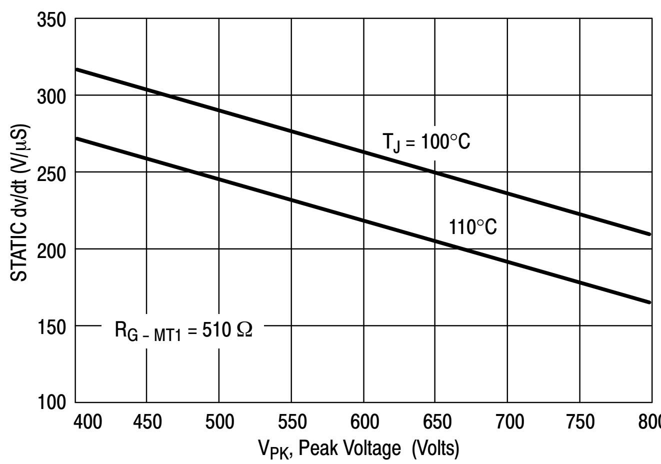


Figure 12. Typical Exponential Static dv/dt Versus Peak Voltage, MT2(−)

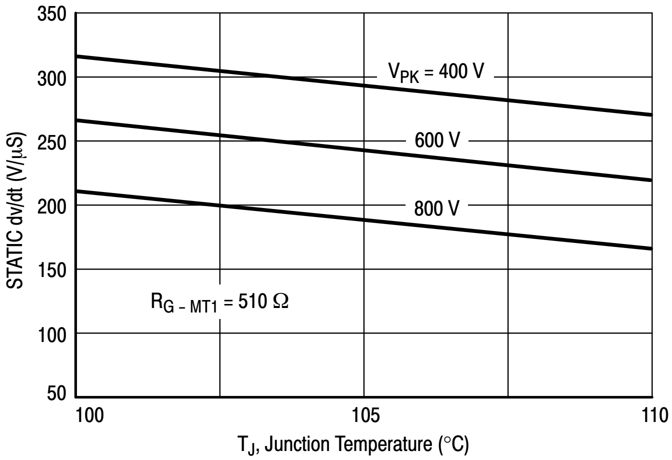


Figure 13. Typical Exponential Static dv/dt Versus Junction Temperature, MT2(−)

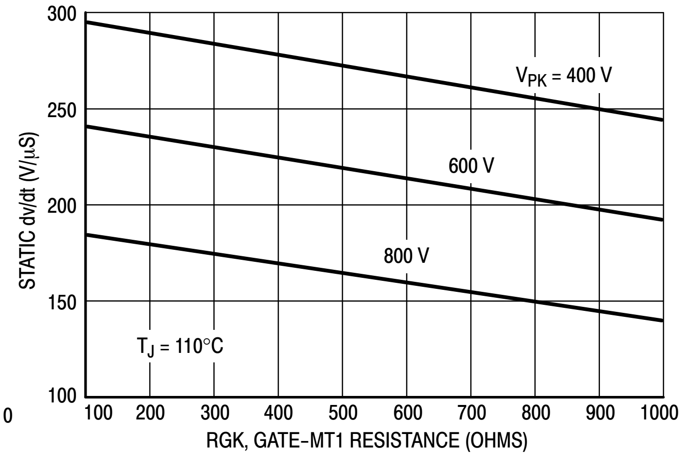


Figure 14. Typical Exponential Static dv/dt Versus Gate−MT1 Resistance, MT2(−)

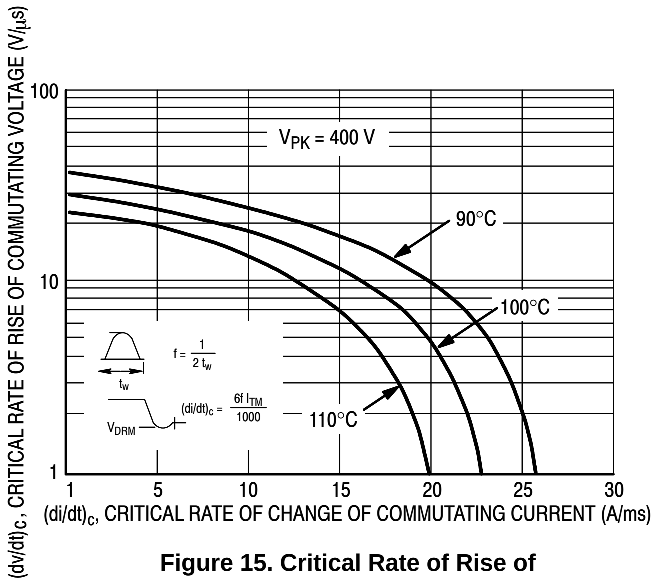
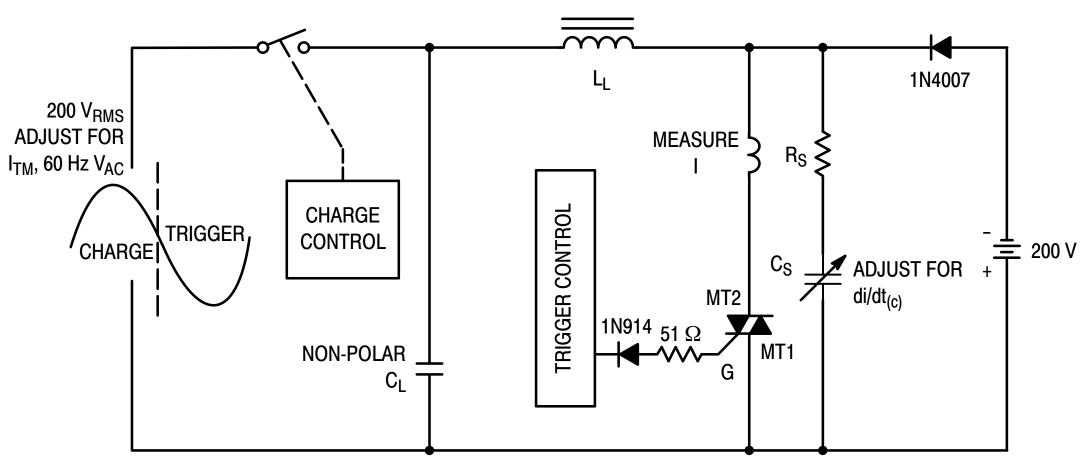


Figure 15. Critical Rate of Rise of Commutating Voltage

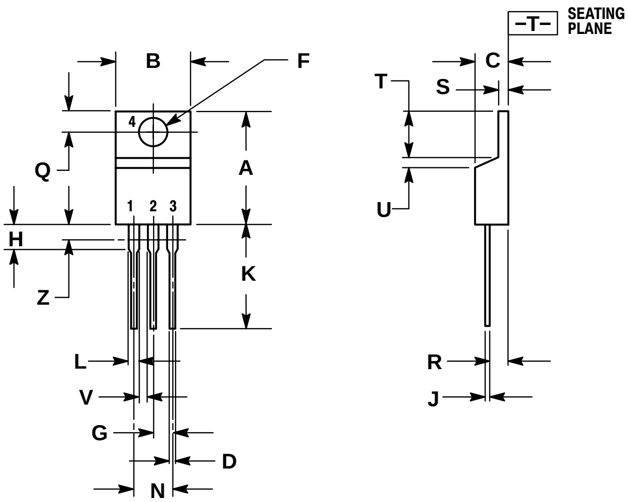


Note: Component values are for verification of rated $(di/dt)_c$. See AN1048 for additional information.

Figure 16. Simplified Test Circuit to Measure the Critical Rate of Rise of Commutating Current $(di/dt)_c$

PACKAGE DIMENSIONS

TO−220
CASE 221A−09
ISSUE AH



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.415	9.66	10.53
C	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

STYLE 4:
PIN 1. MAIN TERMINAL 1
2. MAIN TERMINAL 2
3. GATE
4. MAIN TERMINAL 2

PUBLICATION ORDERING INFORMATION

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